Kanako Shojiki

List of Publications by Year
in descending order

38	516	686830 13	713013 21
papers	citations	h-index	g-index

38	38	38	494
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Emission color modulation of InGaN/GaN multiple quantum wells by selective area metalorganic vapor phase epitaxy on hexagonal windows. Japanese Journal of Applied Physics, 2022, 61, 030904.	0.8	0
2	Centimeter-scale laser lift-off of an AlGaN UVB laser diode structure grown on nano-patterned AlN. Applied Physics Express, 2022, 15, 051004.	1.1	9
3	263 nm wavelength UV-C LED on face-to-face annealed sputter-deposited AlN with low screw- and mixed-type dislocation densities. Applied Physics Express, 2022, 15, 055501.	1.1	21
4	Highâ€Quality AlN Template Prepared by Faceâ€toâ€Face Annealing of Sputtered AlN on Sapphire. Physica Status Solidi (B): Basic Research, 2021, 258, 2000352.	0.7	16
5	Thick AlN layers grown on micro-scale patterned sapphire substrates with sputter-deposited annealed AlN films by hydride vapor-phase epitaxy. Journal of Crystal Growth, 2021, 566-567, 126163.	0.7	6
6	Effect of the Sputtering Deposition Conditions on the Crystallinity of High-Temperature Annealed AlN Films. Coatings, 2021, 11, 956.	1.2	8
7	Thermal strain analysis considering in-plane anisotropy for sputtered AlN on c- and a-plane sapphire under high-temperature annealing. AIP Advances, 2021, 11, .	0.6	3
8	Effect of MOVPE growth conditions on AlN films on annealed sputtered AlN templates with nano-striped patterns. Journal of Crystal Growth, 2021, 570, 126237.	0.7	2
9	Reduction of threading dislocation densities of N-polar face-to-face annealed sputtered AlN on sapphire. Journal of Crystal Growth, 2021, 574, 126309.	0.7	12
10	Highâ€Temperature Annealing of Sputteâ€Deposited AlN on (001) Diamond Substrate. Physica Status Solidi (B): Basic Research, 2020, 257, 1900447.	0.7	2
11	MOVPE growth of AlN films on nano-patterned sapphire substrates with annealed sputtered AlN. Journal of Crystal Growth, 2020, 532, 125397.	0.7	17
12	Annealing behaviors of vacancy-type defects in AlN deposited by radio-frequency sputtering and metalorganic vapor phase epitaxy studied using monoenergetic positron beams. Journal of Applied Physics, 2020, 128, .	1.1	24
13	Toward Bright and Pure Single Photon Emitters at 300 K Based on GaN Quantum Dots on Silicon. ACS Photonics, 2020, 7, 1515-1522.	3.2	36
14	Crystalline quality improvement of face-to-face annealed MOVPE-grown AlN on vicinal sapphire substrate with sputtered nucleation layer. Journal of Crystal Growth, 2020, 545, 125722.	0.7	10
15	Suppression of dislocation-induced spiral hillocks in MOVPE-grown AlGaN on face-to-face annealed sputter-deposited AlN template. Applied Physics Letters, 2020, 116, .	1.5	44
16	Reduction of threading dislocation density and suppression of cracking in sputter-deposited AlN templates annealed at high temperatures. Applied Physics Express, 2019, 12, 065501.	1.1	59
17	Local and anisotropic strain in AlN film on sapphire observed by Raman scattering spectroscopy. Japanese Journal of Applied Physics, 2019, 58, SCCB17.	0.8	11
18	Preparation of high-quality thick AlN layer on nanopatterned sapphire substrates with sputter-deposited annealed AlN film by hydride vapor-phase epitaxy. Japanese Journal of Applied Physics, 2019, 58, SC1003.	0.8	15

#	Article	IF	Citations
19	Curvature-controllable and crack-free AlN/sapphire templates fabricated by sputtering and high-temperature annealing. Journal of Crystal Growth, 2019, 512, 131-135.	0.7	9
20	Quantitative evaluation of strain relaxation in annealed sputter-deposited AlN film. Journal of Crystal Growth, 2019, 512, 16-19.	0.7	27
21	Impact of face-to-face annealed sputtered AlN on the optical properties of AlGaN multiple quantum wells. AIP Advances, 2019, 9, 125342.	0.6	18
22	Fabrication of AlN templates on SiC substrates by sputtering-deposition and high-temperature annealing. Journal of Crystal Growth, 2019, 510, 13-17.	0.7	12
23	Biexciton Emission From Single Quantumâ€Confined Structures in Nâ€Polar (000â€1) InGaN/GaN Multiple Quantum Wells. Physica Status Solidi (B): Basic Research, 2018, 255, 1700454.	0.7	0
24	Quantification of scattering loss of III-nitride photonic crystal cavities in the blue spectral range. Physical Review B, 2017, 95, .	1.1	14
25	Fabrication of Cu2ZnSnS4 thin films using a Cu-Zn-Sn-O amorphous precursor and supercritical fluid sulfurization. Thin Solid Films, 2017, 638, 244-250.	0.8	1
26	Absolute technique for measuring internal electric fields in InGaN/GaN light-emitting diodes by electroreflectance applicable to all crystal orientations. Applied Physics Express, 2017, 10, 082101.	1.1	2
27	Large Stokes-like shift in N-polar $(000ar{1})$ InGaN/GaN multiple-quantum-well light-emitting diodes. Japanese Journal of Applied Physics, 2016, 55, 05FJ03.	0.8	5
28	Nanometer scale fabrication and optical response of InGaN/GaN quantum disks. Nanotechnology, 2016, 27, 425401.	1.3	6
29	Polarity control of GaN grown on pulsed-laser-deposited AlN/GaN template by metalorganic vapor phase epitaxy. Japanese Journal of Applied Physics, 2016, 55, 05FA04.	0.8	5
30	Homogeneity improvement of N-polar $(000ar{1})$ InGaN/GaN multiple quantum wells by usingc-plane sapphire substrate with off-cut-angle towarda-sapphire plane. Japanese Journal of Applied Physics, 2016, 55, 05FA09.	0.8	13
31	Effects of Mg/Ga and V/III source ratios on hole concentration of N-polar $(000ar{1})$ p-type GaN grown by metalorganic vapor phase epitaxy. Japanese Journal of Applied Physics, 2016, 55, 05FE01.	0.8	3
32	Suppression of metastable-phase inclusion in N-polar (0001Â¯) InGaN/GaN multiple quantum wells grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 2015, 106, .	1.5	6
33	Red to blue wavelength emission of N-polar $(000ar{1})$ InGaN light-emitting diodes grown by metalorganic vapor phase epitaxy. Applied Physics Express, 2015, 8, 061005.	1.1	49
34	Enhancement of surface migration by Mg doping in the metalorganic vapor phase epitaxy of N-polar GaN/sapphire. Japanese Journal of Applied Physics, 2014, 53, 05FL05.	0.8	16
35	Effect ofc-plane sapphire substrate miscut angle on indium content of MOVPE-grown N-polar InGaN. Japanese Journal of Applied Physics, 2014, 53, 05FL07.	0.8	7
36	Improvement of surface morphology of nitrogen-polar GaN by introducing indium surfactant during MOVPE growth. Japanese Journal of Applied Physics, 2014, 53, 085501.	0.8	22

#	Article	IF	Citations
37	Investigation of indium incorporation into InGaN by nitridation of sapphire substrate in MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 417-420.	0.8	3
38	Tilted Domain and Indium Content of InGaN Layer on m-Plane GaN Substrate Grown by Metalorganic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2012, 51, 04DH01.	0.8	3